



THE UNITED STATES PATENT AND TRADEMARK OFFICE

Art Unit: 1711
Examiner: R. Sergeant

In Re Application of:

Applicant: LIU et al.

Serial No.: 09/546,174

Filed: April 11, 2000

For: HIGH DENSITY PLASMA
CHEMICAL VAPOR
DEPOSITION PROCESS

Docket No.: JIA 462C1

AMENDMENT

July 2, 2001

TC 1700 MAIL ROOM

JUL - 3 2001

RECEIVED

Commissioner for Patents
Washington, DC 20231

Sir:

Responsive to the Office Action mailed April 3, 2001 please amend the application as follows:

IN THE CLAIMS

Please cancel claims 1-20 without prejudice or disclaimer.

Please add new claims 21 - 37 as follows:

--21. (New) A method for forming isolated conductive structures on a substrate,
comprising:

FEE ENCLOSED: \$
Please charge any further
fee to our Deposit Account
No. 18-0002

a1